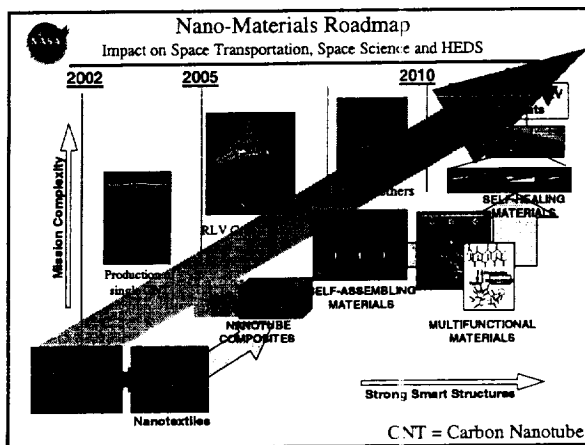
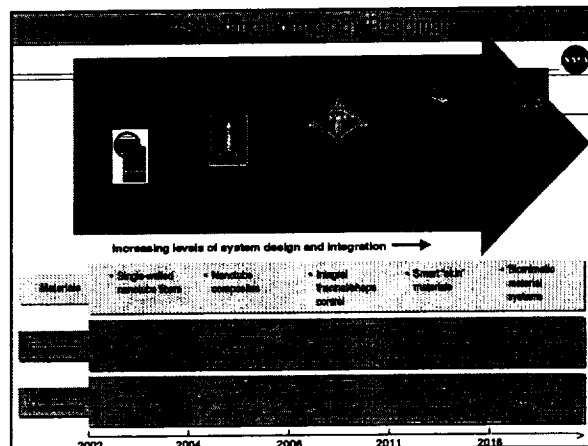
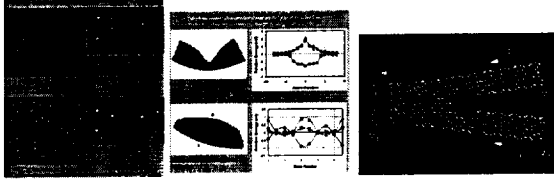


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Deepak Srivastava
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Carbon Nanotube

CNT is a tubular form of carbon with diameter as small as 1 nm. Length: few nm to microns.

CNT is configurationally equivalent to a two dimensional graphene sheet rolled into a tube.

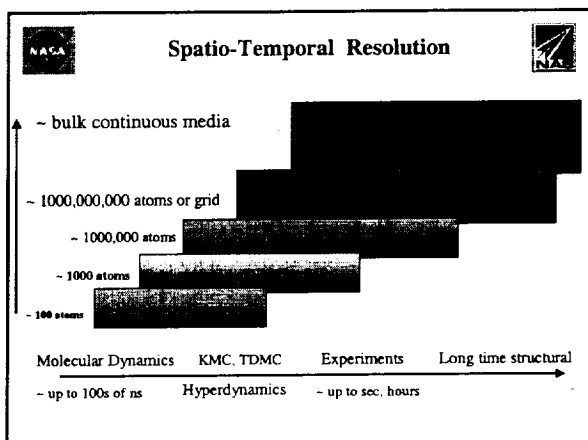
CNT exhibits extraordinary mechanical properties: Young's modulus over 1 Tera Pascal, as stiff as diamond, and tensile strength ~ 200 GPa.

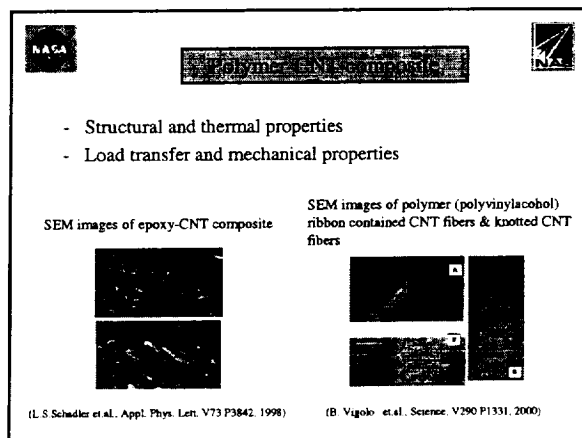
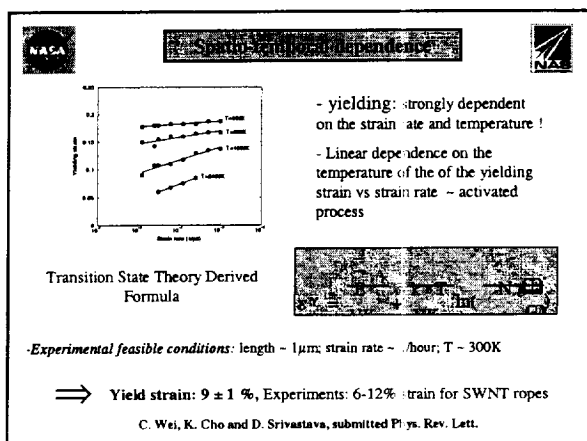
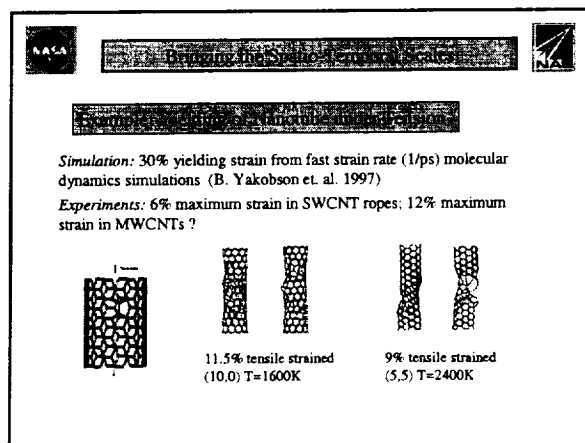
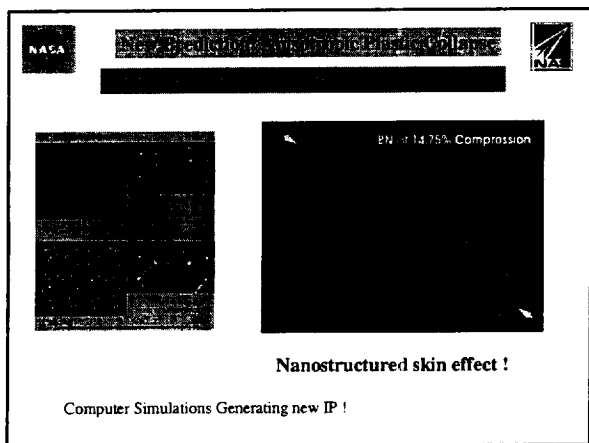
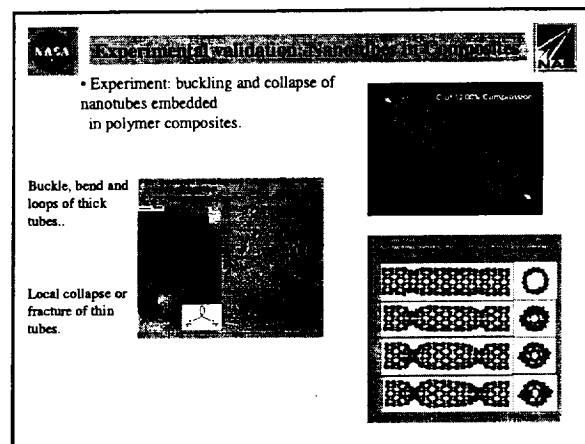
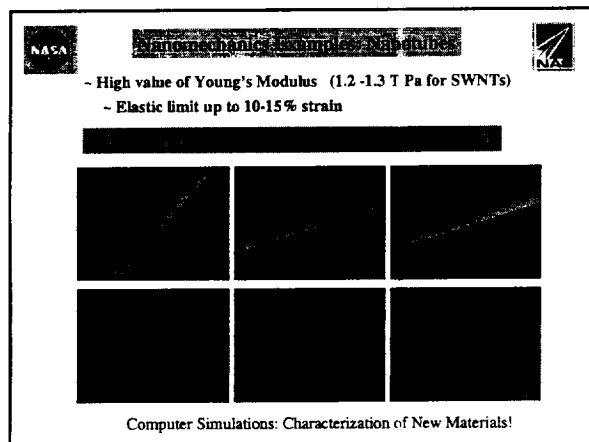
CNT can be metallic or semiconducting, depending on chirality.

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Computational Nanotechnology Project
Grateful Acknowledgement

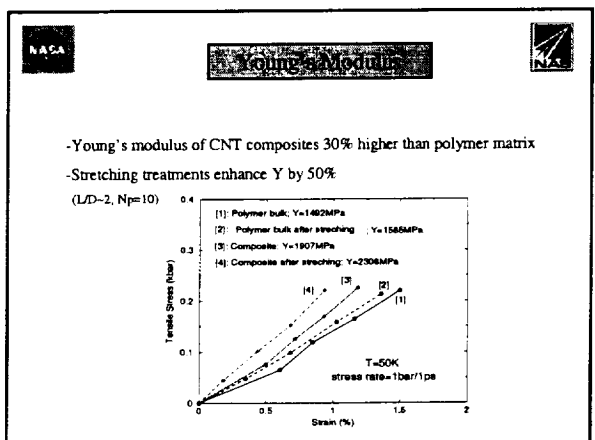
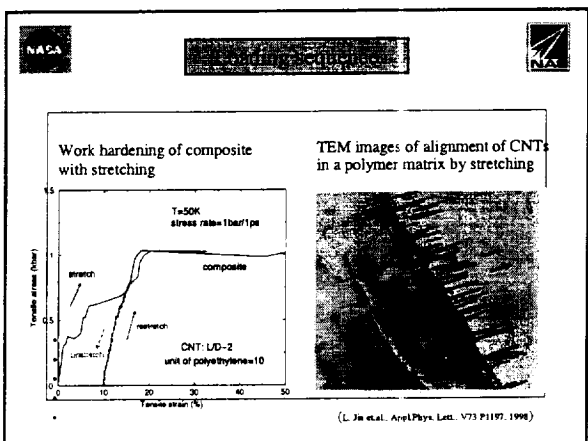
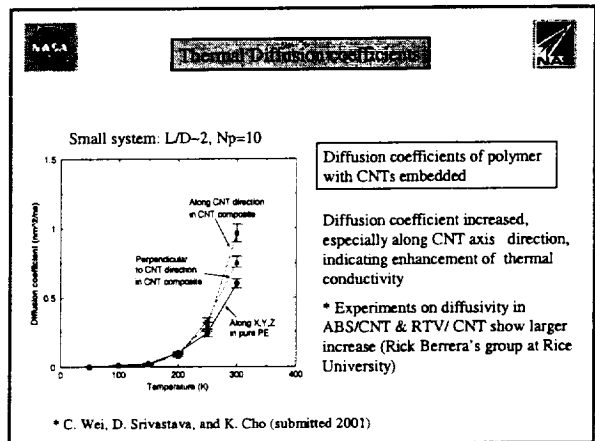
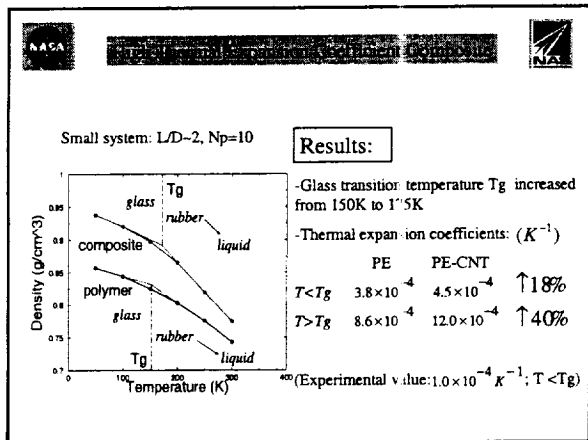
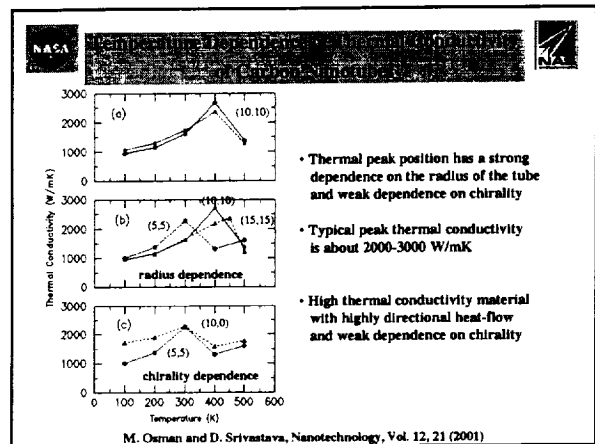
- Nanomechanics of Nanotubes and Nanotube-Polymer Composites
→ Dr. Chengyu Wei (Postdoc), Prof. K. Cho (Stanford University)
- Chemical Functionalization, Thermal Conductivity, Gas Storage
→ Prof. Don Brenner (NC State), Prof. M. Osman (Washington State)
- Molecular Electronics with Nanotube Hetero-junctions
→ Dr. Madhu Menon (U. Ky) and Dr. Antonis Andriotis (U. Crete)
- Quantum Computing with Doped Bucky Onions and Fullerenes
→ Seongjun Park (Student), Prof. K. Cho (Stanford)
- Genetic Algorithm based Searches for New Molecular Force Field
→ Al Globus (NASA Ames)

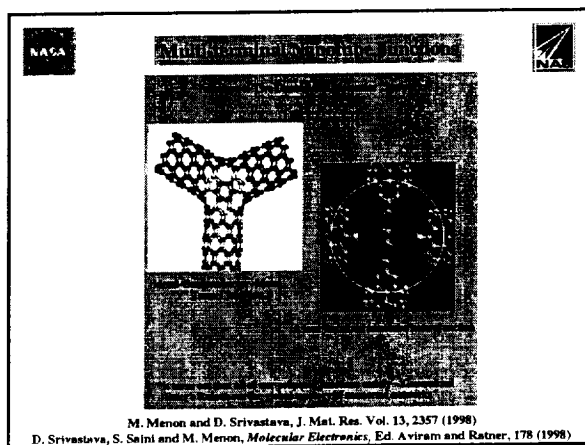
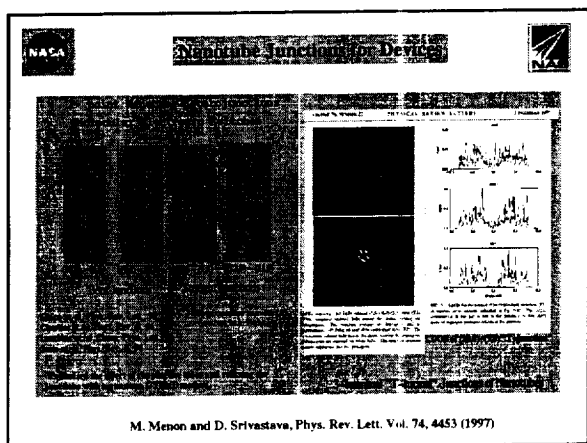
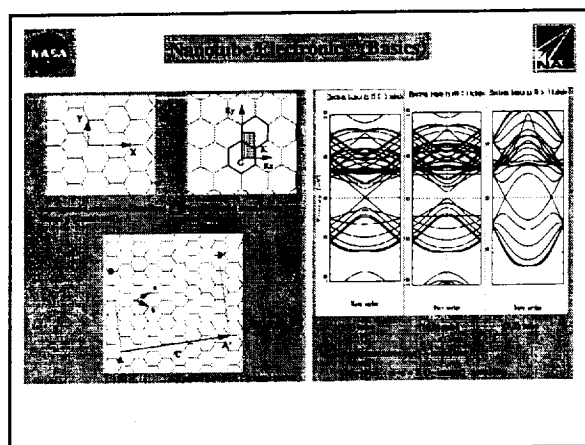
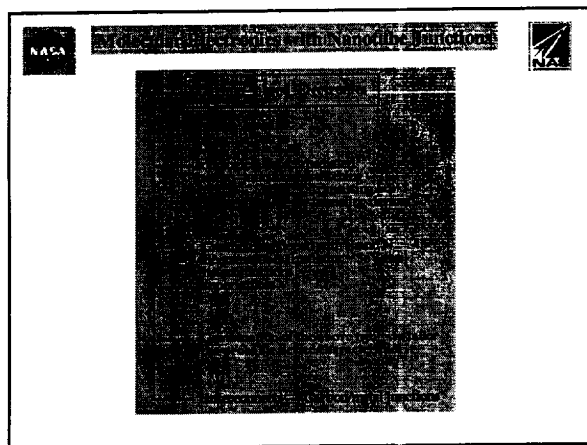
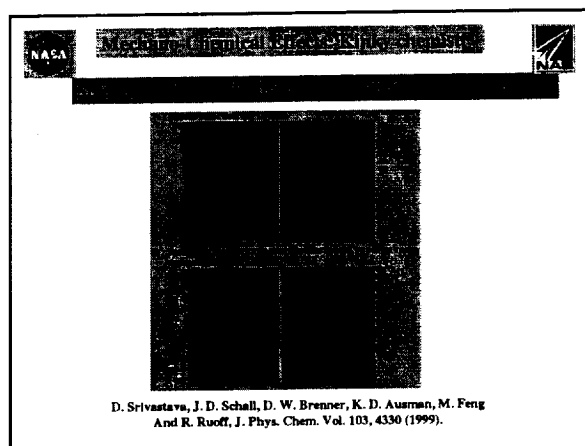
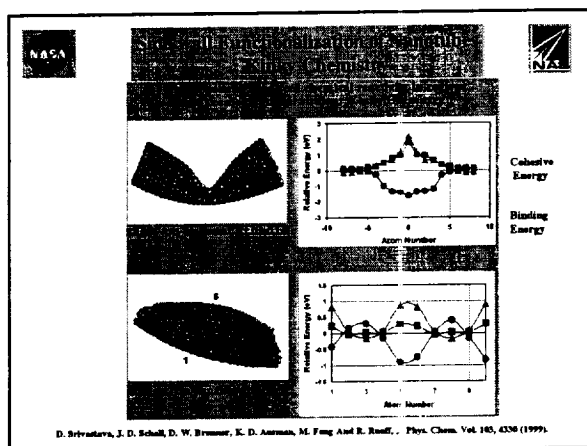


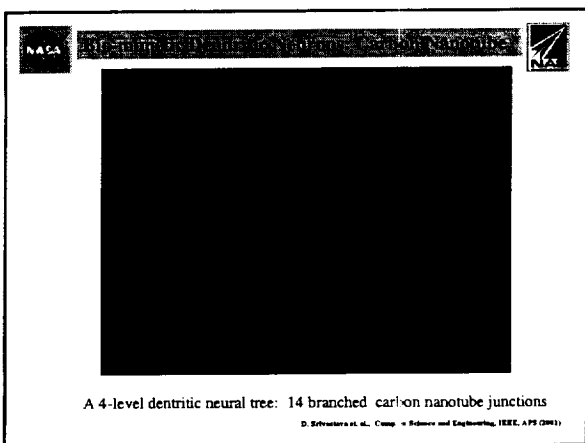
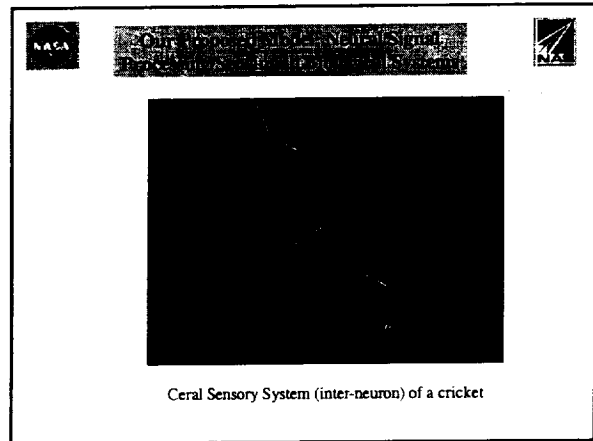
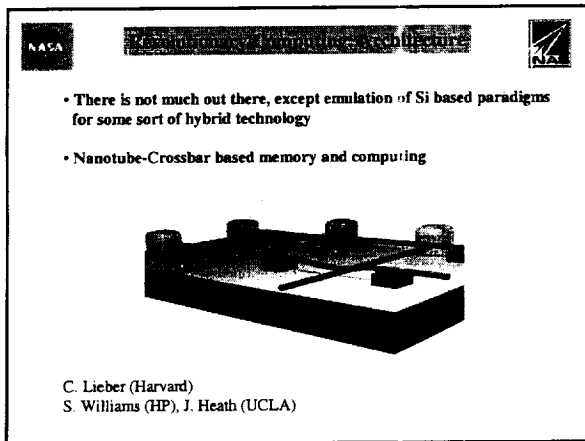
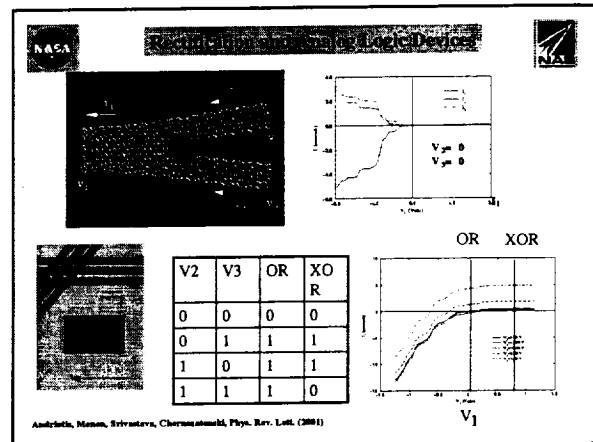
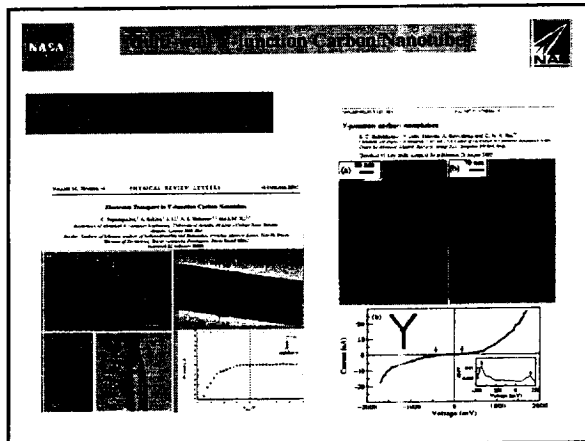


Thermal Conductivity of Nanotube/Polymer Composites

- Thermal conductivity of single-wall nanotubes
- Nanotube/polymer composites as high thermal expansion coefficient materials
- Thermal conductivity of nanotube/polymer composite





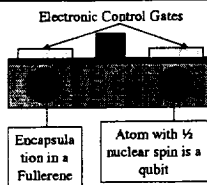


Bio-mimetic Dendritic Neurons: Carbon Nanotubes

Biological Dendritic Neural Tree	Carbon Nanotube: Dendritic Tree
<ul style="list-style-type: none"> • One dimensional cable theory + Hodgkin-Huxley model for action-potential based information flow • Information processing is coded in (a) branching at the junctions, and (b) time-series sequencing of the signal spikes • Input - output - control: is based on (a) structural details of the branches and junctions, and (b) via chemical environment • Short and long term memory is part of the structure: evolutionary in nature 	<ul style="list-style-type: none"> • Electronic, acoustic, thermal, and chemical signal transmission and information processing • Information processing can be based on (a) branching + switching at the junctions, and (b) time series sequencing of signal-spikes • Input - output - control: can be based on (a) structural details, (b) chemical environment, and (c) physical contacts at the ends? • Short and long term memory can be part of structure by defect and chemical adsorbate placements: design for specific purpose/functionality

D. Srivastava et al., Comp. & Biomed. Res., IEEE, APS (2001)

Solution: Use Encapsulated Atoms as Qubits !



Proposal: Arrays of "encapsulated" atoms (with $1/2$ nuclear spin - qubits) will be easy to fabricate as compared to the arrays of the similar bare atoms.

Example: ^1H encapsulated in C_{36}



Electronic charge density shows a weak meta-stable state of ^1H at the center of C_{36}

Suitable Solid-state Qubits Identified:

- ^1H encapsulated in a $\text{C}_{36}\text{D}_{20}$ fullerene
- ^{31}P encapsulated in a diamond nanocrystallite

Charge Density of ^1H Encapsulated in $\text{C}_{20}\text{D}_{20}$

- The valance electron charge density of ^1H leaks out of $\text{C}_{20}\text{D}_{20}$ cage molecule. This is good and needed for neighboring qubit interactions.



S. Park, D. Srivastava and K. Cho, J. NanoSc. NanoTech. (2001)

Model 2: ^{31}P doped in Diamond or Silicon

- Weakly bound donor electron has strong S-like electronic charge density at the center, and a reasonable spread of the decay for off center positions



^{31}P in Diamond



^{31}P in Si

S. Park, D. Srivastava and K. Cho, J. NanoSc. and NanoTech. (2001)



J. Han, A. Globus and R. Jaffe



Model 2: ^{31}P doped in Diamond or Silicon



Nanomaterials and Nanotechnology



Nanomaterials and Nanotechnology



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